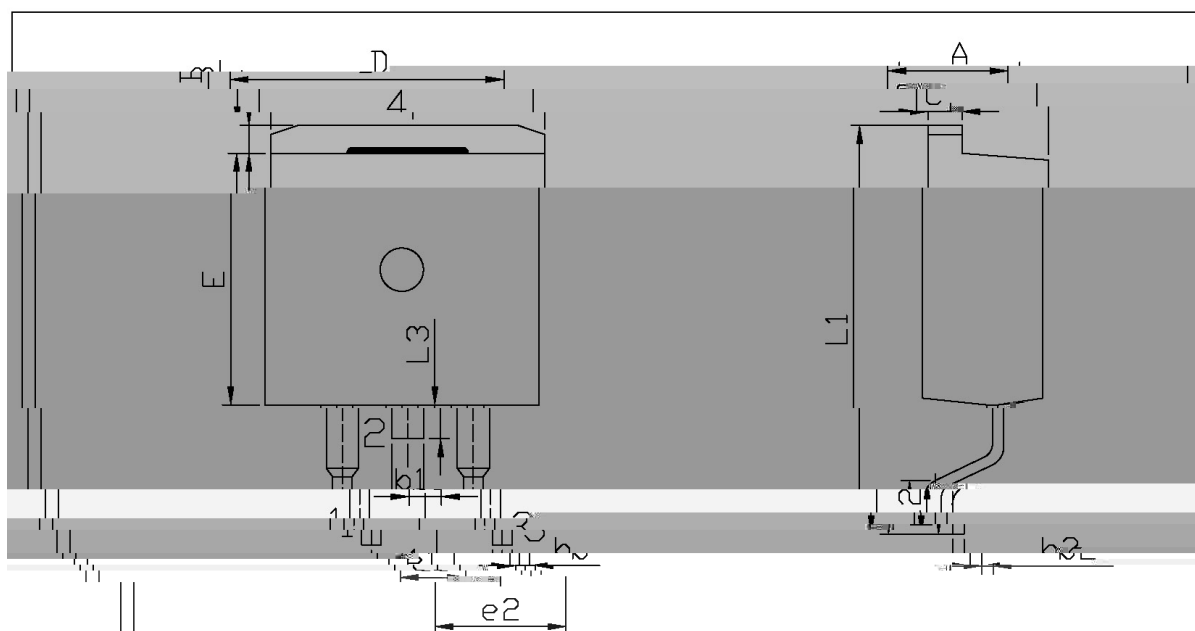
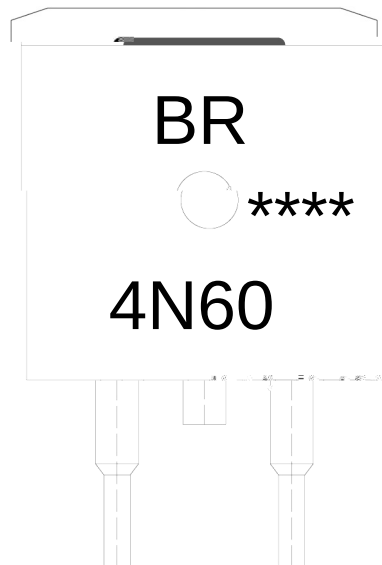


Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	600	V
Drain Current	$I_D(T_c=25^\circ\text{C})$	4.0	A
Drain Current	$I_D(T_c=100^\circ\text{C})$	2.5	A
Drain Current - Pulsed	I_{DM}	16	A
Gate-Source Voltage	V_{GSS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	240	mJ
Repetitive Avalanche Energy	E_{AR}	10	mJ
Avalanche Current	I_{AR}	4.0	A
Power Dissipation	$P_D(T_c=25^\circ\text{C})$	100	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	600			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=600V$ $V_{GS}=0V$			10	μA
		$V_{DS}=480V$ $T_C=125^\circ\text{C}$			100	μA
Gate-Body Leakage Current, Forward	I_{GSS}	$V_{GS}=\pm 30V$ $V_{DS}=0V$			± 0.1	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2.0		4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=2.0A$		2.0	2.5	Ω
Forward Transconductance	g_{FS}	$V_{DS}=40V$ $I_D=2.0A$		4.7		S
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=4.0A$			1.4	V
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		545	710	pF
Output Capacitance	C_{oss}			60	80	pF
Reverse Transfer Capacitance	C_{rss}			8	11	pF
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=300V$ $I_D=4.0A$ $R_G=25\Omega$		10	30	ns
Turn-On Rise Time	t_r			35	80	ns
Turn-Off Delay Time	$t_{d(off)}$			45	100	ns
Turn-Off Fall Time	t_f			40	90	ns



Dimensions in Millimeters		Dimensions in Millimeters	
Max	Min	Max	Min
9.40	4.30	4.70	0.00
2.34	1.00	1.40	2.34
0.00	0.00	0.00	0.00



BR

4N60

Note:

BR: Company Code

4N60: Product Type.

****: Lot No. Code, code change with Lot No.

